

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1 - 11 (canceled)

12. (currently amended) A plasma processing apparatus for processing a product using plasma, comprising:

a power source for applying bias power to an electrode on which a substrate to be processed is disposed;

an insulating layer formed on a surface of said electrode on which said substrate to be processed is disposed;

a first conductive material formed within said insulating layer in a ring-like form;

a first feeder line connecting said power source and said first conductive material;

a first variable capacitor provided in said first feeder line;

a silicon ring mounted at a position surrounding the substrate to be processed, on the surface of said electrode on which the substrate to be processed is disposed;

a second conductive material formed within said insulating layer and under said silicon ring;

a second feeder line connecting said power source and said second conductive material; and

a second variable capacitor provided in said second feeder line;  
wherein one portion of said insulating layer formed on an outer part of said electrode where said first conductive material and said second conductive material are formed has a thickness which is greater than a thickness of another portion of said insulating layer formed on a central part of said electrode where said first conductive material and said second conductive material are not formed.

13. (previously presented) The apparatus according to claim 12, wherein said insulating layer formed on the surface of said electrode includes alumina.

Claim 14 (canceled)

15. (currently amended) The apparatus according to claim 14 12, wherein a part the one portion of said insulating layer is formed on is disposed under said first conductive material and said second conductive material, and between said first conductive material and said electrode, and between said second conductive material and said electrode, and the another portion said electrode, the another position of said insulating layer is formed at the central being a center portion part of said electrode thereof.

16. (currently amended) A plasma processing apparatus for processing a product using plasma, comprising:

a high-frequency power source for applying bias power to an electrode on which a substrate to be processed is disposed;

an insulating layer formed on a surface of said electrode on which said substrate to be process is disposed;

a conductive material formed within said insulating layer in a ring-like form;

a feeder line connecting said high-frequency power source and said conductive material;

a variable capacitor provided in said feeder line; and

a direct current power source connected between said electrode and said high frequency power source;

wherein one portion of said insulating layer formed on an outer part of said electrode where said conductive material is formed has a thickness which is greater than a thickness of another portion of said insulating layer formed on a central part of said electrode where said conductive material is not formed.

17. (currently amended) The apparatus according to claim 15 16, wherein a ~~first resonance coil~~ coils are ~~is~~ coupled to ~~said~~ variable capacitor ~~provided on~~ between ~~said~~ feeder line, and ~~said~~ electrode and ~~a second resonance coil is~~ provided between ~~said~~ direct current power source and ~~said~~ electrode, respectively.

18. (new) The apparatus according to claim 12, wherein said insulating layer at the one portion where said first conductive material is formed has three times the thickness of said insulating layer at the central part where said first conductive material and said second conductive material are not formed.

19. (new) The apparatus according to claim 12, wherein said insulating layer at the one portion where said second conductive material is formed has two

times the thickness of said insulating layer at the central part where said first conductive material and said second conductive material are not formed.